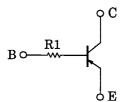
TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

## RN2110F,RN2111F

Switching, Inverter Circuit, Interface Circuit and Driver Circuit Applications

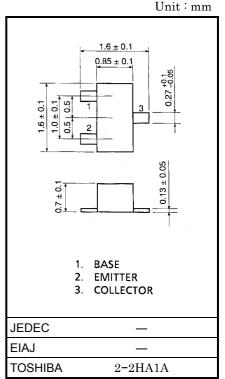
- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process
- Complementary to RN1110F, RN1111F

## **Equivalent Circuit**



## Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V <sub>CBO</sub>	-50	V
Collector-emitter voltage	V <sub>CEO</sub>	-50	V
Emitter-base voltage	V <sub>EBO</sub>	-5	V
Collector current	Ι <sub>C</sub>	-100	mA
Collector power dissipation	P <sub>C</sub>	100	mW
Junction temperature	Tj	150	°C
Storage temperature range	T <sub>stg</sub>	-55~150	°C



Weight : 2.3mg

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damage to property.
In developing, your designs, places onsure that TOSHIBA products are used within specified operating ranges as set forth in the

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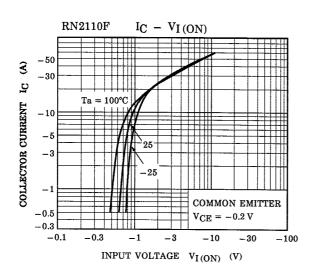
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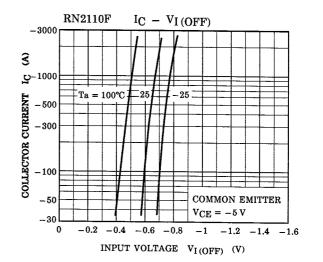
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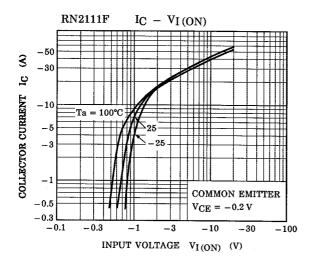
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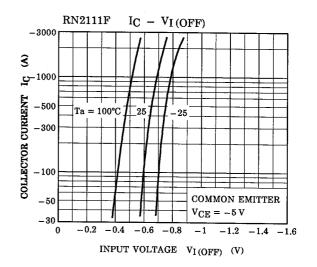
**Electrical Characteristics (Ta = 25°C)** 

Characteristic		Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current		I <sub>CBO</sub>	_	$V_{CB} = -50V, I_E = 0$	_	_	-100	nA
Emitter cut-off current		I <sub>EBO</sub>	_	$V_{EB} = -5V, I_C = 0$	_	_	-100	nA
DC current gain		h <sub>FE</sub>	-	$V_{CE} = -5V$ , $I_C = -1mA$	120	_	400	
Collector-emitter saturation voltage		V <sub>CE (sat)</sub>	_	I <sub>C</sub> = −5mA, I <sub>B</sub> = −0.25mA	_	-0.1	-0.3	V
Transition frequency		f <sub>T</sub>	—	V <sub>CE</sub> = −10V, I <sub>C</sub> = −5mA	_	200	_	MHz
Collector output capacitance		C <sub>ob</sub>	—	$V_{CB} = -10V, I_E = 0, f = 1MH_z$	_	3	6	pF
Input resistor	RN2110F	R1			3.29	4.7	6.11	kΩ
	RN2111F				7	10	13	

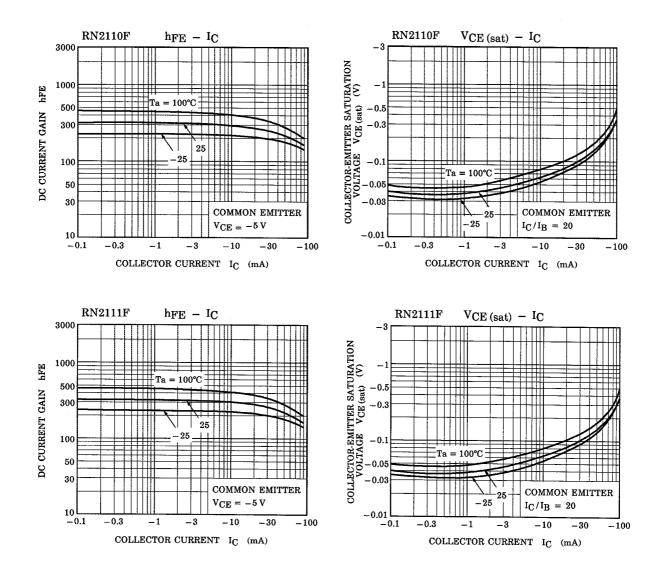








## TOSHIBA



Type Name	Marking	
RN2110F	Type Name	
RN2111F	Type Name Y M	